

DOCKET NO: 264197US0PCT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
SHINSUKE SADAMITSU, ET AL. : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. APPLICATION :
BASED ON PCT/JP03/08333
FILED: HEREWITH :
FOR: HIGH-RESISTANCE SILICON :
WAFER AND PROCESS FOR :
PRODUCING THE SAME

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 5 of this paper.